Page 1 of 5

PATENT NO. : 6,838,307 B2

hereby corrected as shown below:

DATED : January 4, 2005 INVENTOR(S) : Gilton

It is certified that error appears in the above-identified patent and that said Letters Patent is

### Title page,

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, the following should be included:

inciaaca.		
6,673,648	1/2004	Lowrey
2004/0035401	2/2004	Ramachandran et al.
2003/0212724	11/2003	Ovshinsky et al.
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PATENT NO. : 6,838,307 B2 Page 2 of 5 DATED : January 4, 2005

INVENTOR(S) : Gilton

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page (cont'd),		
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PATENT NO. : 6,838,307 B2

DATED

: January 4, 2005

INVENTOR(S) : Gilton

Page 3 of 5

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page (cont'd),			
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FOREIGN PATENT DOCUMENTS,			
"WO	WO 99/28194	6/1999" should read	
WO	WO 99/28914	6/1999	

PATENT NO. : 6,838,307 B2

DATED : January 4, 2005 INVENTOR(S) : Gilton Page 4 of 5

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

#### Title page (cont'd),

- "Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilay r electrode, Thin Solid Films 131 (1985) L61-L64." should read
- -- Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64. --; "Guin, J.-P.; Roux, I, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J.,
- Indentation creep of Ge-Se chalcogenide galss s glass s below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269." should read
- -- Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269. --;
- "Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clust ring f Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142." should read
- -- Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142. --;
- "Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. L tt. 46 (1985) 543-545." should read
- -- Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545. --;
- "McHardy et al., The dissolution of metals in am rphous chalcogenid s and the eff cts o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f" should read
- -- McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987) --;
- "Messoussi, R.; Berneda, J.C.; Benhide, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=N), i.Bi Mat. Chem. And Phys. 28 (1991) 253-258." should read
- -- Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258. --;
- "Popescu, C.; Croitoru, N., The contribution of the lateral thermal Instability to th switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537." should read
- -- Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537. --;
- "Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphou s lenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73." should read
- -- Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73. --;

PATENT NO. : 6,838,307 B2 DATED : January 4, 2005

INVENTOR(S) : Gilton

Page 5 of 5

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

#### Title page (cont'd),

- "Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 48 B. Chem Soc. Japan, No. 12, pp. 3662-3365 (1973)." should read
- -- Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 46 B, Chem. Soc. Japan, No. 12, pp. 3662-3365 (1973). --; and
- "Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the Islope dTg/d<m>lat the rigidity percolation threshold (<m>x2.4), J. Non-Cryst. Solids 151 (1992) 149-154." should read
- -- Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope ldTg/d<m>| at the rigidity percolation threshold (<m>x2.4), J. Non-Cryst. Solids 151 (1992) 149-154. --.

#### Column 2,

Line 51, "and" should read -- an --;

### Column 6,

Line 2, "ovelying" should read -- overlying --; Line 58, "provide" should read -- provided --; and Line 60, "contining" should read -- containing --.

Signed and Sealed this

Sixth Day of December, 2005

JON W. DUDAS Director of the United States Patent and Trademark Office